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For

SEMICONDUCTOR DEVICE HAVING A PAD METAL LAYER AND A LOWER METAL
LAYER THAT ARE ELECTRICALLY COUPLED, WHEREAS APERTURES ARE FORMED IN
THE LOWER METAL LAYER BELOW A CENTER AREA OF THE PAD METAL LAYER

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SEMICONDUCTOR DEVICE HAVING A PAD METAL LAYER AND A LOWER METAL LAYER THAT ARE ELECTRICALLY COUPLED, WHEREAS APERTURES ARE FORMED IN THE LOWER METAL LAYER BELOW A CENTER AREA OF THE PAD METAL LAYER

5 BACKGROUND OF THE INVENTION

FIELD OF THE INVENTION

The present invention generally relates to semiconductor devices. More particularly, the present invention relates to the electrically coupling a pad metal layer and a lower metal layer in a semiconductor device.

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RELATED ART

The semiconductor fabrication process generally includes a probing process. In the probing process, a probe instrument is utilized to make mechanical and electrical contact with the exposed surface of the pad metal of an integrated circuit chip (or die). Voltage or current is then applied through the probe instrument to test for functionality. Unfortunately, the probe instrument may induce stress on the pad metal such that the stress propagates to lower layers of the integrated circuit chip. As a result, a layer(s), such as an interlayer dielectric between metal layers, can crack and become damaged, leading to reliability problems. Similarly, the wire-bonding process can cause cracking and damage to a layer(s) of the integrated circuit chip.

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Figure 1A illustrates a cross-sectional view of a semiconductor structure 100 of a conventional integrated circuit chip. As shown in Figure 1A, the semiconductor structure 100 includes a pad metal layer 10 having an exposed surface 12, an interlayer dielectric (ILD) 40, and a lower metal layer 20. Moreover, the semiconductor structure 100 further includes an insulating dielectric 30 that covers the perimeter area of the pad metal layer 10. Additionally, the semiconductor structure 100 includes a plurality of vias 25 formed in the interlayer dielectric (ILD) 40 to electrically couple the pad metal layer 10 and the lower metal layer 20. As depicted in Figure 1A, the vias 25 are formed below the exposed surface 12 of the pad metal layer 10. This illustrates how the stress, induced by the probe instrument, propagates to lower layers of the integrated circuit chip through the vias 25.

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A top view of the semiconductor structure 100 of the conventional integrated circuit chip of Figure 1A is shown in Figure 1B. The top view of Figure 1B depicts the insulating dielectric 30 and the exposed surface 12 of the pad metal layer 10. Moreover, the symbols 60 illustrate the position of the vias 25 below the pad metal layer 10.

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SUMMARY OF THE INVENTION

A semiconductor device is disclosed and provided. The semiconductor device includes a pad metal layer having a perimeter area and a center area. Further, the semiconductor device has a lower metal layer having a plurality of apertures below the center area of the pad metal layer. Moreover, an interlayer dielectric is formed between the pad metal layer and the lower metal layer. In an embodiment, the semiconductor device also includes a plurality of vias formed in the interlayer dielectric. The vias electrically couple the pad metal layer and the lower metal layer. Additionally, the vias are located below the perimeter area of the pad metal layer.

These and other advantages of the present invention will no doubt become apparent to those of ordinary skill in the art after having read the following detailed description of the preferred embodiments, which are illustrated in the drawing figures.

BRIEF DESCRIPTION OF THE DRAWINGS

The accompanying drawings, which are incorporated in and form a part of this specification, illustrate embodiments of the invention and, together with the description, serve to explain the principles of the present invention.

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Figure 1A illustrates a cross-sectional view of a semiconductor structure of a conventional integrated circuit chip.

10 Figure 1B illustrates a top view of the semiconductor structure of the conventional integrated circuit chip of Figure 1A.

Figure 2 illustrates a cross-sectional view of a semiconductor structure of a semiconductor device in accordance with an embodiment of the present invention.

15 Figure 3A illustrates a top view of the pad metal layer of the semiconductor structure of the semiconductor device of Figure 2.

20 Figure 3B illustrates a top view of the semiconductor structure of the semiconductor device of Figure 2.

Figure 4 illustrates a top view of the lower metal layer of the semiconductor structure of the semiconductor device of Figure 2.

25 Figure 5 illustrates a flow chart showing a method of electrically coupling a pad metal layer and a lower metal layer in a semiconductor device in accordance with an embodiment of the present invention.

The drawings referred to in this description should not be understood as being drawn to scale except if specifically noted.

DETAILED DESCRIPTION OF THE INVENTION

Reference will now be made in detail to the preferred embodiments of the present invention, examples of which are illustrated in the accompanying drawings. While the invention will be described in conjunction with the preferred embodiments, it will be understood that they are not intended to limit the invention to these embodiments. On the contrary, the invention is intended to cover alternatives, modifications and equivalents, which may be included within the spirit and scope of the invention as defined by the appended claims. Furthermore, in the following detailed description of the present invention, numerous specific details are set forth in order to provide a thorough understanding of the present invention.

Figure 2 illustrates a cross-sectional view of a semiconductor structure 200 of a semiconductor device in accordance with an embodiment of the present invention. In an embodiment, the semiconductor device is an integrated circuit chip. As shown in Figure 2, the semiconductor structure 200 includes a pad metal layer 210 having an exposed surface 212, an interlayer dielectric (ILD) 240, and a lower metal layer 220.

Moreover, the semiconductor structure 200 further includes an insulating dielectric 230 that covers the perimeter area of the pad metal layer 210. Also, the lower metal layer 220 has a plurality of apertures 260 below the center area (or exposed surface 212) of the pad metal layer 210, whereas the interlayer dielectric (ILD) 240 can fill the apertures 260. Additionally, the semiconductor structure 200 includes a plurality of vias 225 formed in the interlayer dielectric (ILD) 240 to electrically couple the pad metal layer 210 and the lower metal layer 220. In an embodiment, the vias 225 are filled with tungsten.

Unlike in Figure 1A, the vias 225 are formed below the perimeter area of the pad metal layer 210 rather than below the center area (or exposed surface 212) of the pad metal layer 210. This relieves the stress induced by performing the probing process or the wire-bonding process since the center area (or exposed surface 212) usually experiences the most amount of stress that can be propagated to lower layers. Moreover, the amount of stress that propagates to lower layers of the integrated circuit chip through the vias 225 is significantly reduced, decreasing cracking and damage to lower layer(s) of the integrated circuit chip.

It should be understood that the semiconductor structure 200 can also be implemented such that a metal layer(s), which is below the lower metal layer 220, has a plurality of apertures similar to the apertures 260 of the lower metal layer 220. Moreover, the vias between the lower metal layer 220 and this metal layer can be located below the vias 225 between the pad metal layer 210 and the lower metal layer 220 to form a linear vertical arrangement of vias.

Figure 3A illustrates a top view of the pad metal layer of the semiconductor structure 200 of the semiconductor device of Figure 2. The top view of the pad metal layer 210 is depicted, showing the perimeter area 270 and the center area (or exposed area) 212 of the pad metal layer 210. Moreover, the symbols 275 illustrate the position of the vias 225 below the pad metal layer 210. As illustrated in Figure 3A, the vias 225 are positioned in a ring arrangement below the perimeter area 270 of the pad metal layer 210.

Moreover, in Figure 3B a top view of the semiconductor structure 200 of the semiconductor device of Figure 2 is shown. The top view of Figure 3B depicts the insulating dielectric 230 and the center area (or exposed surface) 212 of the pad metal layer 210. Unlike Figure 1B, the vias 225 are located below perimeter area 270 (Figure 3A) of the pad metal layer 210, whereas the perimeter area 270 is covered by the insulating dielectric 230.

Figure 4 illustrates a top view of the lower metal layer 220 of the semiconductor structure 200 of the semiconductor device of Figure 2. The lower metal layer 220 has a plurality of apertures 260 below the center area (or exposed surface 212) of the pad metal layer 210. Moreover, the vias 225 are in a ring arrangement around the apertures 260. Also, the interlayer dielectric (ILD) 240 fills the apertures 260.

The pitch, dimensions, and number of apertures 260 can be selected such that release of sufficient stress (e.g., caused by the probing process or the wire-bonding process) is achieved to avoid cracking and damage to lower layer(s) of the integrated circuit chip.

Figure 5 illustrates a flow chart showing a method 50 of electrically coupling a pad metal layer and a lower metal layer in a semiconductor device in accordance with an embodiment of the present invention. In an embodiment, the semiconductor device is an integrated circuit chip.

At Step 510, a plurality of apertures are formed in the lower metal layer. The pad metal layer has a perimeter area and a center area. The apertures are located below the center area (or exposed surface) of the pad metal layer

Continuing, at Step 520, a plurality of vias are formed in an interlayer dielectric between the pad metal layer and the lower metal layer. The vias are located below the perimeter area of the pad metal layer.

Moreover, at Step 530, the vias are filled with a metal. In an embodiment, the metal is tungsten. Hence, this electric coupling method addresses the cracking and damage to lower layer(s) of the integrated circuit chip.

The foregoing descriptions of specific embodiments of the present invention have been presented for purposes of illustration and description. They are not intended to be exhaustive or to limit the invention to the precise forms disclosed, and many modifications and variations are possible in light of the above teaching. The embodiments were chosen and described in order to best explain the principles of the invention and its practical application, to thereby enable others skilled in the art to best utilize the invention and various embodiments with various modifications as are suited to the particular use contemplated. It is intended that the scope of the invention be defined by the Claims appended hereto and their equivalents.